

# Publications -Robert G. Elliman

## Book Chapters [1-6]

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## Journal Papers [7-233]

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- [13]. M.G. Lemaitre, S. Tongay, X. Wang, D.K. Venkatachalam, J. Friedmann, B.P. Gila, A.F. Hebard, F. Ren, R.G. Elliman and B.R. Appleton, "*Low-Temperature, Site Selective Graphitization of SiC via Ion Implantation and Pulsed Laser Annealing*", Appl. Phys. Lett. 100, 193105 (4 Pages) (2012)
- [14]. R.G. Elliman, T.H. Kim, A. Shalav and N.H. Fletcher, "*Controlled Lateral Growth of Silica Nanowires and Coaxial Nanowire Heterostructures*", J. Phys. Chem. C 116, 3329-3333 (2012)
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